

VISVESVARAYA TECHNOLOGICAL UNIVERSITY



MINI PROJECT REPORT ON “REVERSE CAR PARKING SENSOR ”

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ENGINEERING



DEPARTMENT OF ELECTRONICS AND
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CERTIFICATE

Certified that the mini project work entitled “**Reverse car parking sensor**” carried out by **Mouneesh (1NH18E011)** bonafide students of Electronics and Communication Department, New Horizon College of Engineering, Bangalore.

The mini project report has been approved as it satisfies the academic requirements in respect of mini project work prescribed for the said degree.

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ABSTRACT

Reverse car parking sensor it adopts infra-red light sensors which measure the distance accurately when reversing a car. This circuit was designed as an aid in parking the car near the garage well when backing up. In this manner we are alerted when approaching too close to the wall. The first LED illuminates when bumper-wall distance is about 65cm, 1 more LED illuminates at about 50cm, and in all 3 LEDs at about 45cm. In this way it is provided with the visual feedback

This reverse car parking sensor circuit solve all these problems. You can easily install at the backside of your car. You can also use the mass shadow alarm at door to protect your car. When shadow of an intruder fall on it will also give you alarm. This alarm will provide you the musical sound that's why it will not tease your ears.

Reverse car parking sensor circuit solves this problem by inducting the distance with the help of three LED's. We can easily arrange this system at the backside of the car. This system operates with 9v rechargeable battery.

This Reverse car parking sensor circuit is quite easy and use few commonly available components which are resistors, LED's, battery, ICLM358, buzzer, etc.

CHAPTER 1

INTRODUCTION

We are often afraid that our brand new Hummer is going to get scratched while parking it in the tight space. Or we have trouble backing our large Mercedes S- class into our small garage. There is no need to fear anymore! This car parking sensor circuit can sense how far we are away from the wall or a hidden object behind your car and warn us visually using LEDs. It is to note that we have kept our project scope only till the visual feedback using infra- red technology.

A significant portion of the people around the world own cars or are daily drivers. Among these drivers, it's not entirely untrue to assume that parallel parking or rearward parking is one of the most cumbersome parts of their driving experience. It takes years of driving experience and rigorous practices to avoid an ugly scratch across the bumper. Some old school auto- enthusiasts may like to do everything manually, but most of us like to take advantage of the advanced car electronics and technologies to make our life a little bit easier and also to avoid common accidents during parking. Hence, we decided to design and build an infra-red parking assistant system that will help the driver get a sense of how far the car is away from a wall or an object behind the car.

CHAPTER 2

LITERATURE SURVEY

Intelligent Transportation Systems are defined as those systems utilizing synergistic technologies and systems engineering concepts to develop and improve transportation systems of all kinds. The scope of this interdisciplinary activity include the promotion, consolidation and coordination of ITS technical activities among IEEE entities and providing a focus for cooperative activities, both internally and externally.

In urban areas, congested traffic results in a large number of accidents at low speeds. This paper describes an accurate and fast driver assistance system (DAS) that detects obstacles and warns the driver in advance of possible collisions in such a congested traffic environment. A laboratory prototype of the system is built and tested by simulating different weather conditions in the laboratory. The proposed DAS is also suitable as parking.

IR sensors are used for more appropriate for target which can measure the distance of the object which may not be easily detected by ultrasonic sensors.

A review of automobile-guidance research projects carried out in European universities and advanced safety vehicle development by Japanese car manufacturers is followed by a description of driver assistance systems in current use. A new research initiative for autonomous unmanned aircraft is then discussed. Fully autonomous prototype vehicle have demonstrated impressive feats on public roads, but car manufacturers are currently concentrating on driver assistance systems. Research is underway to extend the use of unmanned aircraft into the civil field, and to allow them to share airspace with piloted planes. Present current policies in automotive and aerospace development, and describes the range of sensor technologies applied to collision avoidance.

Chapter: 3

Principle and Working

Principle

Reverse car parking sensor is a project that operates on IR power supply. The reverse car parking sensor is a circuit that works on the concept of 2 main components that is ICLM358, IR transmitter receiver.

To design this car parking system circuit, we placed an IR transmitter receiver pair at the rear side of the car. IR transmitter transmits infrared signal or rays into the environment continuously. When these transmitted IR rays reflect back to IR receiver after striking on an obstacle, some voltage difference generates across this IR receiver LED. This generated voltage difference depending upon the power of IR rays that are reflected back to the receiver. More powered signal leads to more voltage difference. This voltage difference is used in our project to measure the distance. Here more voltage difference indicates the lesser distance from the object. Here we have shown distance from the obstacle by using three LED's. meaning of these LED'S are explained in working of this project.

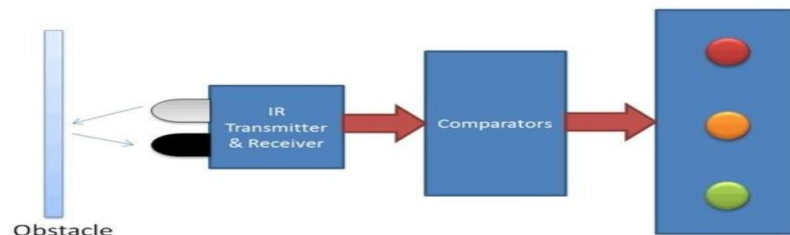


Fig 3.1

Circuit Diagram and Explanation

In this car parking circuit we have used an IR pair for detecting obstacle and two LM358 dual comparator ICs for comparing voltages. Comparator configured in non-inverting mode and 10K

potentiometer is connected at its inverting terminal for adjusting reference voltage and IR receiver's output is directly connected at non-inverting pins of all comparators. One red LED is connected at output of U1: BIC(LM358), a yellow LED is connected at output pin of U2:A IC(LM358) And an Green LED is connected at output pin of U2:B IC(LM358) a 1K resistor. A buzzer is also added at Red LED.

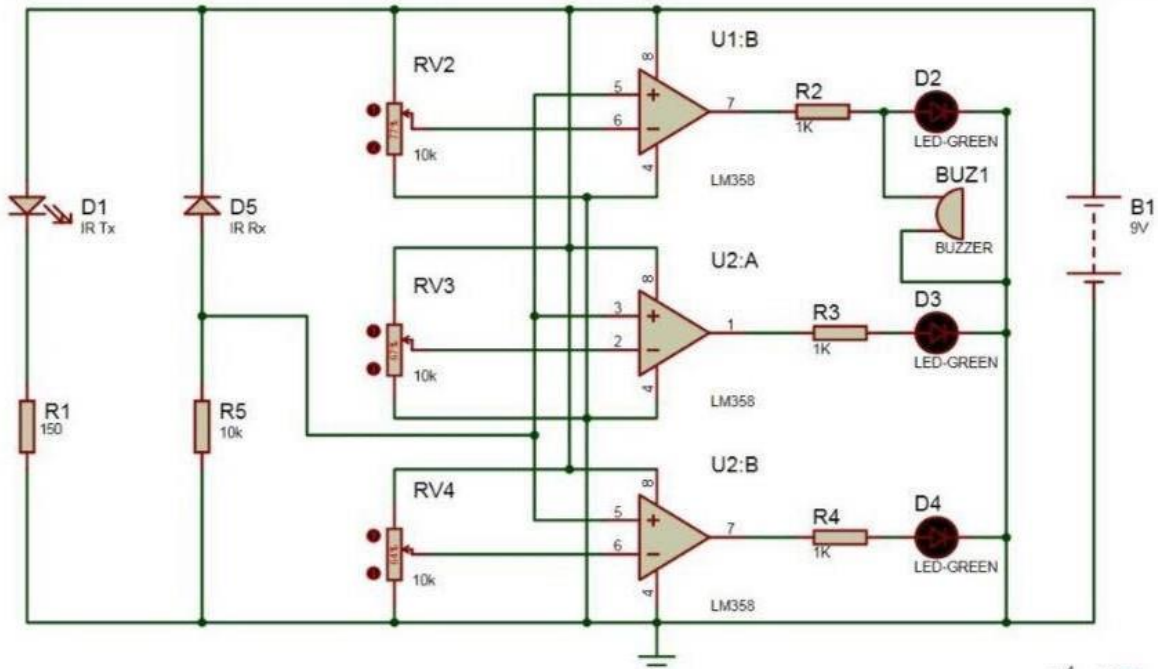


Fig 3.2

Working

We have shown the reference voltage and relative parameters in the below table. But one can set distance by changing the value of potentiometer

Obstacle v/s Vehicle	LED status	Reference Voltage	Distance
not close	All OFF		Greater than 15 cm
Close	Green ON	2.0 Volt	About 15 cm
More Close	Yellow ON	4.0 Volt	About 10 cm
More Close	Red ON	6.0 Volt	About 5 cm
Touch	Car Damaged		About 0 cm

Fig 3.3

This system is placed at the rear of the car and sensor's front side toward the obstacle (wall). Now suppose car is moving back toward the wall or obstacle in the parking slot. If distance between car and obstacle is more than 15 cm then no LED will glow. Now if car moves toward the obstacles and suppose green light turned on, it means car is about 15 cm away from the obstacle. Now car is moving more close toward the obstacle and yellow light appears or turned on it means car is about 10 cm away from the obstacle. Now car is moving closer toward the obstacle and red light appears it means car is about 5 cm away from the obstacle and same time buzzer start beeping. Buzzer and red light indicates that the car need to stop now otherwise car may be damaged.

CHAPTER-4

PROJECT DESCRIPTION

1. IC LM358:

LM358 is a great, low power and easy use with dual channel op-amp. It consists of two internally frequency compensated, high gain, independent op-amps. This is specially designed to operate from a single power supply over a wide range of voltages.

Pin configuration is given as:

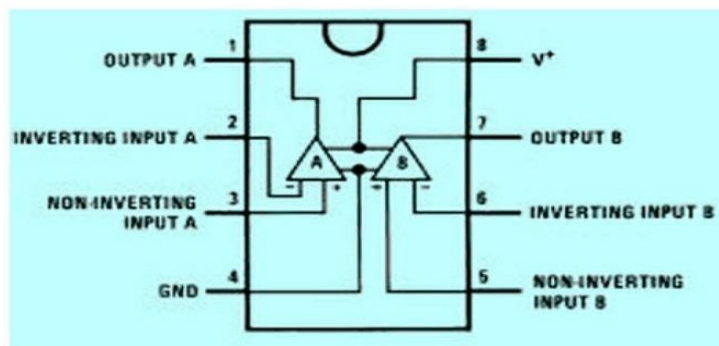


Fig 1.a:pin configuration of LM358

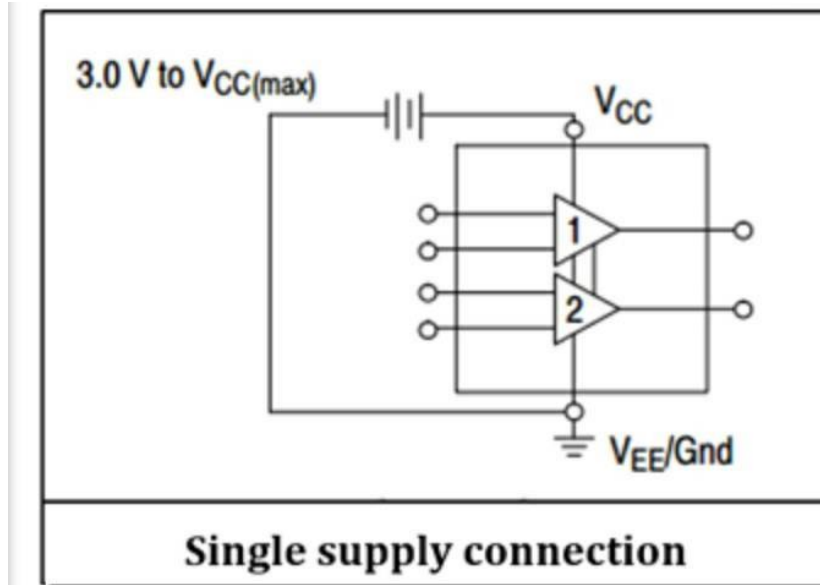


Fig 1.b: Singlesupply connection

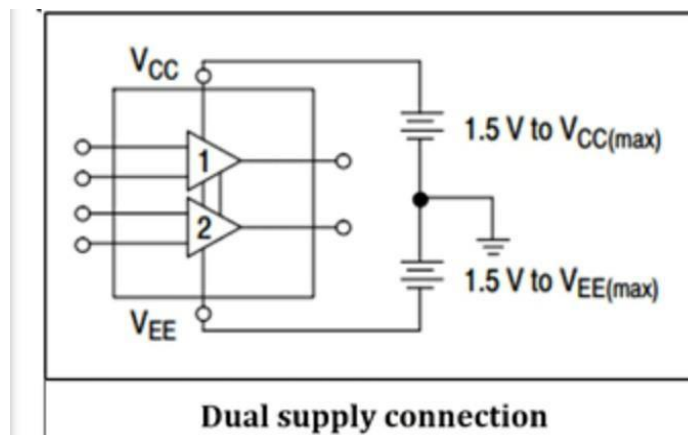


fig 1.c: Dual supply connections

If the inverting pin is HIGH, the output is NEGATIVE
 If the inverting pin is LOW, the output is POSITIVE
 If the non-inverting pin is HIGH, the output is POSITIVE
 If the non-inverting pin is LOW, the output is NEGATIVE

Features of LM358:

1. It consists of two op-amps internally and frequency compensated for unity gain.
2. Max voltage gain of 100dB
3. Max wide of bandwidth is 1MHz
4. It includes both single and dual power supplies
5. Single power supply ranges from 3V to 32V
6. Dual power supply ranges from -1.5V to -16V
7. Drain current is very low i.e, is 500uA
8. Low input offset voltage of 2mV
9. Common mode input voltage comprises to ground
10. Output swing is large

Applications:

1. Transducer amplifiers
2. Conventional op-amp circuits
3. Integrator, differentiator, summer, adder, voltage follower
4. Dc gain blocks, digital multi-meters, oscilloscopes
5. Comparators

2. Resistor

A resistor is passive two-terminal electrical component that implements electrical resistance as a circuit element. In electronic circuits, resistors are used to reduce current flow, adjust signal levels, to divide voltage, bias active elements, and terminate transmission lines, among other uses. High-power resistors that can dissipate many watts of electrical power as heat, may be used as part of motor controls, in power distribution systems, or as test loads for generators.

Fixed resistors have resistances that only change slightly with temperature, time or operating

voltage. Variable resistors can be used to adjust circuit elements (such as a volume control or a lamp dimmer), or as sensing devices for heat, light, humidity, forces, or chemical activity.



Fig2.1

Resistors are common elements of electrical networks and electronic circuits and are ubiquitous in electronic equipment. Practical resistors as discrete components can be composed of various compounds and forms. Resistors are also implemented within integrated circuits. The electrical function of a resistor is specified by its resistance: common commercial resistors are manufactured over a range of more than nine orders of magnitude. The nominal value of the resistance falls within the manufacturing tolerance, indicated on the component.

3. Potentiometer (pot):

A potentiometer is a three-terminal resistor with a sliding or rotating contact that forms an adjustable voltage divider. If only two terminals are used, one end and the wiper, it acts as a variable resistor or rheostat.



Fig:3.1

The measuring instrument called a potentiometer is essentially a voltage divider used for measuring electric potential. The component is an implementation of the same principle, hence its name.

Potentiometers are commonly used to control electrical devices such as volume controls on audio equipments. Potentiometers are operated by a mechanism and can be used as position transducers, for example, in a joystick. Potentiometers are rarely used to directly control significant power since the power dissipated in the potentiometer would be comparable to the power in the controlled load.

There are a number of terms in the electronics industry used to describe certain types of potentiometers:

- ★ **Slide pot or slider pot:** A potentiometer that is adjusted by sliding the wiper left or right, usually with a finger or a thumb.
- ★ **Thumb pot or thumbwheel pot:** A small rotating potentiometer meant to be adjusted infrequently by means of a small thumbwheel.
- ★ **Trim pot or trimmer pot:** A trimmer potentiometer typically meant to be adjusted once or infrequently for "fine-tuning" an electrical signal.

4. Power Supply:

A power supply is a device that supplies electric power to an electric load. The term is the most commonly referred to electric power that converts one form of electrical energy to another, though it may also refer to that which converts another form of mechanical, chemical or solar energy to

electrical energy. The regulated power supply is that controls the output voltage or current to a specific value.

5.LED Working

The light emitting diode (LED) is a two-lead semiconductor light source. In 1962, Nick Holonyak came up with an idea of light emitting diode, and he was working for the general electric company. The LED is a special type of diode and they have similar electric characteristics of a PN junction diode. Hence the LED allows the flow of current in the forward direction and blocks the current in the reverse direction. The LED occupies the small area which is less than the 1mm^2 .

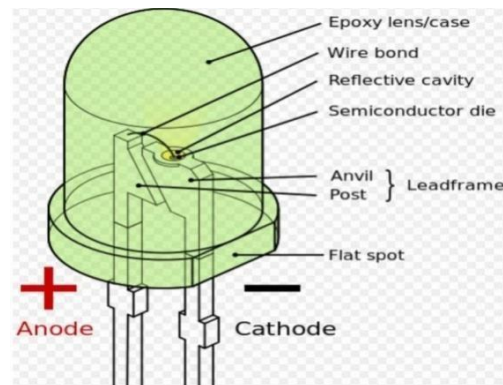


Fig 5.1

Light Emitting Diode

The light emitting diode simply, we know as a diode. When the diode is forward biased, then the electrons and holes are moving fast across the junction and they are combining constantly, removing one another out. Soon after the electrons are moving from the n-type to the p-type silicon, it combines with the holes, and then it disappears. Hence it makes the complete atom and more stable and it gives the little burst of energy in the form of a tiny packet or photon of light.

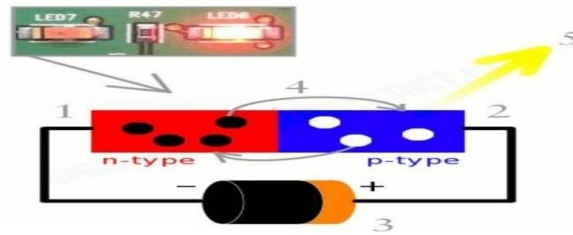


Fig5.2

Working of Light Emitting Diode

The above diagram shows how the light emitting diode works and the step by step process of the diagram.

From the diagram, we can observe that the N-type silicon is in red color and it contains the electrons, they are indicated by the black circles.

The P-type silicon is in the blue color and it contains holes, they are indicated by the white circles.

The power supply across the p-n junction makes the diode forward biased and pushing the electrons from n-type to p-type pushing the holes in the opposite direction.

The electron and holes at the junction are combined.

The photons are given off as the electrons and holes are recombined.

Fabrication of LED device

GaN and the related group 3 nitrides are key materials in high-efficiency LED's. Most of the commercially available GaN-based LED's have been fabricated by MOCVD on single crystalline Sapphire wafers because of their high thermal and chemical stability. However, application of GaN based on LED's 'those are often restricted because of the use of sapphire as the substrate for GaN epitaxy has significant problems of small area, high cost, and difficulty in processing.

GaN on sapphire also suffers from large mismatches in lattice constants (16%) and thermal expansion Coefficient (34%), which leads to the formation of high-density crystalline defects in

GaN films. To address these issues and expand the application field of GaN-based LED's, a technique to grow high-quality GaN films on alternative substrate needs to be developed.

Metal have recently emerged as a promising substrate for this purpose, since metal foils generally possess flexibility and high thermal and electrical conductivity, and large-area metal foils can be prepared by a rolling process at a reasonable cost. Among various metals, hafnium (Hf) is an ideal substrate material for GaN growth because it shares many similarities in structural properties with GaN, including a similar space symmetry group ($P6/mmc$ (Hf) and $P6mc$ (GaN)) and small mismatches in the axis lattice constant (0.3%) and the thermal expansion coefficient (5.3%) between GaN and Hf.

Despite these advantages, GaN growth on a Hf foil has not been practical because of two significant problems. One problem is the randomly oriented grains of commercially available Hf foils, which lead to poor crystalline quality of the overlaid GaN film. To solve this problem, a highly c-axis oriented Hf foil with a large grain size should be prepared before GaN growth.

Annealing can be a simple approach to promote recrystallization of a metal foil, which can produce a highly oriented structure. The other problem is the serious interfacial reactions between GaN and Hf during high-temperature growth in conventional techniques such as MOCVD. The interfacial reactions must be suppressed to grow high-quality GaN films on Hf foils. Recent progress in the epitaxial growth process based on PDS has made it possible to grow high-quality group 3 atoms during PDS growth. Such LT growth can suppress the interfacial reactions between GaN and a chemically vulnerable substrate such as metals. In fact, LT epitaxial growth of GaN and AlN films on various single-crystalline metal substrates has been achieved. It should be noted that PDS is capable of industry-scale growth of GaN due to its high productivity and scalability. In this study, we investigated GaN growth on Hf foils by PDS and explored the feasibility of GaN based full color LED's on the Hf foils.

A scanning electron microscope (SEM) image of an as-received 50- μm -thick Hf shows the foil surface to be rough (Fig. 1a), as expected from the rolling process for producing foils. The halo reflection high-energy diffraction (RHEED) pattern in the inset of Fig. 1a indicates that the

surface is covered with an amorphous oxide layer. Fig 1b shows the crystal orientation map collected by election backscattered diffraction(EBSD) in the normal direction of the surface.

The randomly oriented grains with a size as small as $5\mu\text{m}$. To improve the crystalline quality and surface smoothness of Hf foils, we annealed the foils above 1000°C in vacuum .

After annealing, the surface smoothness was drastically improved, as seen in the SEM image of Fig.1c.

A sharp streaky diffraction pattern was seen in RHEED observation (inset of Fig.1c), indicating removal of the amorphous oxide layer and appearance of crystalline Hf with the smooth surface.

Fig 1d shows the EBSD crystal orientation map along the surface normal direction. One can clearly see that the annealed Hf foils have highly c-axis oriented structure in the entire area.

Also, the map in the rolling direction revealed that the grain size of the annealed c-axis oriented Hf foils was as large as $500\mu\text{m}$, as shown in Fig.1e. X-ray diffraction(XRD) measurements were also performed to investigate the before and after annealing .As shown in Fig .1f, the as-received Hf foil showed multiple peaks indicating randomly oriented crystalline structure, while only {0001} related diffraction peaks were observed for the annealed Hf foil.

These XRD data are consistent to the EBSD results. The full width at half- maximum (FWHM) value of 0002 x-ray rocking curve (XRC) of the annealed Hf foil was as small as 151 arcsec , which is attributed to the highly c-axis orientation of the annealed Hf foil. These results indicates process makes the Hf foils suitable for GaN crystalline growth.

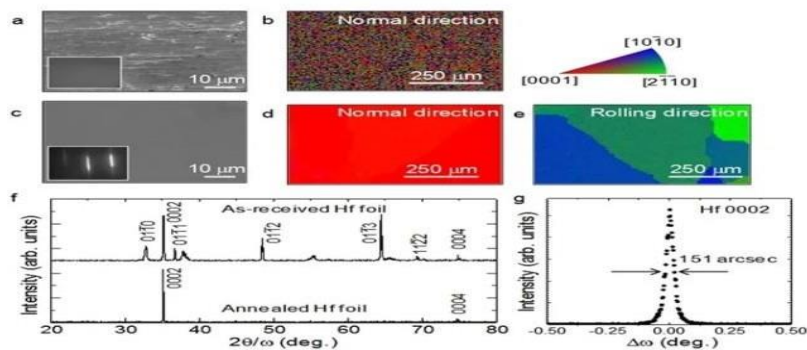


Fig.5.3

Surface structure and crystal orientations of Hf foils. (a) SEM image and (b) EBSD crystal orientation map along surface normal direction for the as-received Hf foil. (c) SEM image for the annealed Hf foil. (d and e) EBSD crystal orientation maps along the surface normal and rolling directions for the annealed Hf foil, respectively. Insets of (a and c) show RHEED patterns. (f) XRD curves of the as-received and annealed Hf foils. (g) XRC for the Hf 0002 diffraction of the annealed Hf foil. After the Hf foil was annealed, a 1 μm -thick GaN film was grown by PDS with a LT-grown reaction barrier layer. SEM observations showed that the GaN film surface is smooth (Fig. 2a), and atomic force microscope (AFM) observations revealed the surface has step-and-terrace structures with a root-mean-square (rms) value of 2.0 nm (inset of Fig. 2a), which indicates that GaN growth is two-dimensional. Fig. 2b illustrates the cross-section transmission electron microscope (TEM) image of the GaN film on the Hf foil. The heterointerface between GaN and Hf was smooth and sharp, indicating that introduction of the LT-grown reaction barrier layer significantly suppresses the interfacial reaction during GaN growth on Hf. Fig. 2c shows EBSD pole figures for $20 \times 20 \mu\text{m}^2$ area of the GaN film. The {0001} spot for the GaN film was sharp and the {1124} pole figures showed a clear six-fold rotational symmetry. This result indicates that the GaN has a single domain structure, at least in the EBSD scanned area ($20 \times 20 \mu\text{m}^2$), due to the constraint from Hf atoms. To investigate the crystalline quality of the GaN film, XRC measurements were performed (Fig. 2d). The FWHM values of 0002 and 1012 XRCs of the GaN film were 324 and 684 μrad , respectively. It should be noted that these values are comparable to those on conventional substrates such as sapphire or Si. Fig. 2e shows the photoluminescence (PL) spectrum of the GaN film at RT. The GaN film exhibited a sharp near-band-edge emission from a hexagonal phase at around 3.4 eV, with the FWHM value as small as 38 meV. From these results, we infer that the use of LT-growth by PDS enables the production of epitaxial GaN films on Hf foils without interfacial reactions, which can be potentially used for fabrication of electronic devices.

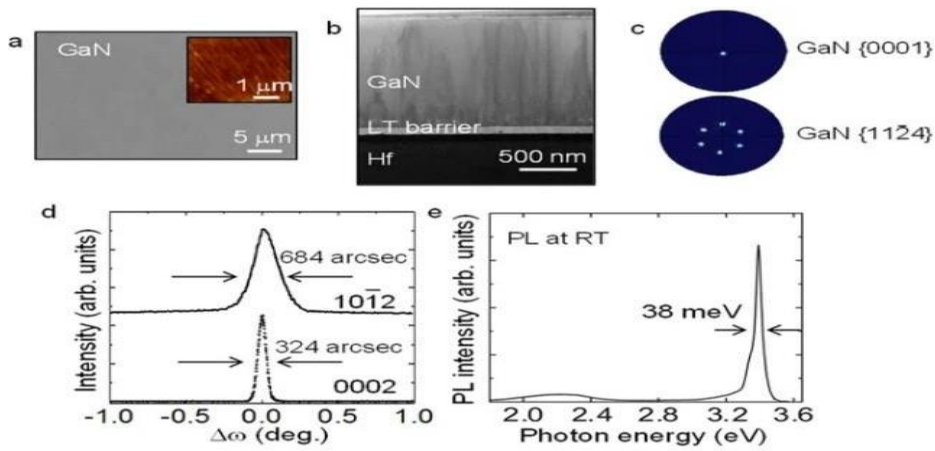


Fig 5.4

Structural and optical properties of GaN film on Hf foil with a LT-grown reaction barrier layer.

(a) Surface SEM and (b) cross-sectional TEM images of the GaN film. Inset of (a) is a surface AFM image. (c) EBSD pole figures of {0001} GaN and {1124} GaN. (d) 0002 and 1012 XRDs, and (e) a RT-PL spectrum of the GaN film.

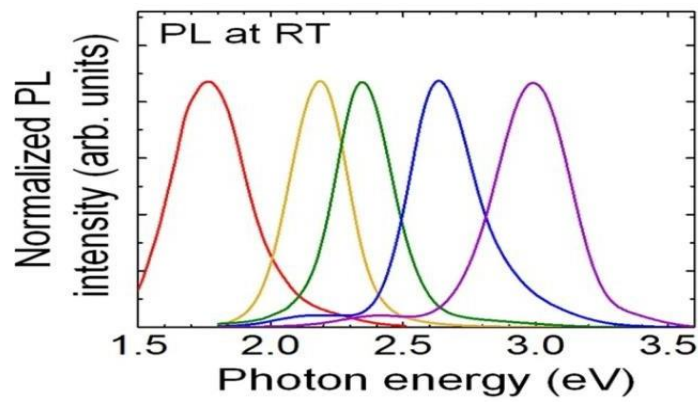


Fig 5.5

Optical properties of InGaN films. RT-PL spectra of InGaN films with various compositions.

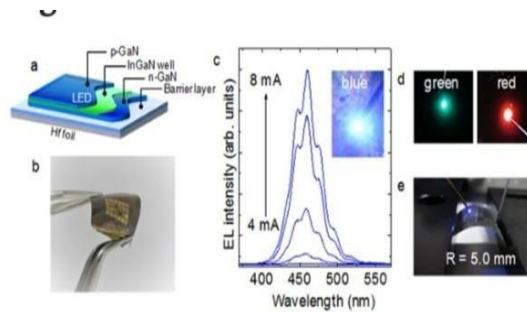


fig 5.6

Fabrication of LEDs on Hf foils. (a) Schematic illustration of an LED structure. (b) Optical image of a flexible Hf foil with a GaN-based LED array. (c) EL spectra of the LED structure at forward currents ranging from 4 to 8 mA. The inset shows an optical image of blue EL at a forward current of 8 mA. (d) Photographs during the operation of green and red LEDs. (e) Light emission photograph at a bending radius of 5.0 mm.

6. Buzzer:

A buzzer or a beeper is an audio signalling device which may be mechanical, electromechanical, or piezoelectric. Typical uses of buzzers and beepers include alarm devices, timers, and confirmation of user input such as a mouse click or keystroke.



Fig 6.1

Types of buzzers:

Electromechanical: Early devices were based on an electromechanical system identical to an

electric bell without the metal gong. Similarly a relay may be connected to

interrupt its own actuating current, causing the contacts to buzz. Often these units were anchored to a wall or ceiling to use it as a sounding board. The word “buzzer” comes from the rasping noise that electromechanical buzzers made.



Fig 6.2

Mechanical: A joy buzzer is an example of a purely mechanical buzzer and they require drivers. Other examples of them are doorbells.



Fig 6.3

Piezoelectric: A piezoelectric element may be driven by an oscillating electronic circuit or other audio signal source, driven with a piezoelectric audio amplifier. Sounds commonly used to indicate that a button has been pressed are click, a ring or a beep.

Piezoelectric



Piezoelectric disk beeper

Fig 6.4

A piezoelectric buzzer also depends on acoustic cavity resonance or Helmholtz resonance to produce an audible beep.

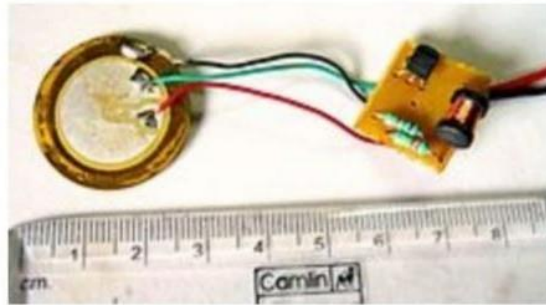


Fig 6.5

7. IR Pair:

Sensors are basically electronic devices which are used to sense the changes that occur in their surroundings. The change may be in color, temperature, moisture, sound, heat etc. They sense the change and work accordingly. In IR sensor there is emitter and detector. Emitter emits the IR rays and detector detects it.

The IR sensor basically consists of three components: IR

LED (emitter)

Photodiode (detector)

Op-Amp

IR LED:



Fig 7.1

IR LED is a light emitting diode which emits the IR radiations. The basic function of the emitter is to convert electricity into light. It works on the principle of combination of electron-hole pair. As in the conduction band of a diode, electrons are the majority carrier and in the valence band, holes are majority carrier. So when an electron from a conduction band recombines with a hole of valence band, some amount of energy is released and this energy is in the form of light. The amount of energy released depends upon the forbidden energy gap. The IR LED has two legs, the leg which is longer is positive and other leg is negative.

Photo diode



Fig 7.2

The photo diode is a p-n junction diode which is connected in reverse bias direction. The basic function of the detector is to convert light into electricity. As its name implies that it works effectively only when the certain number of photon or certain amount of light falls on it. When there is no fall of light on the photodiode it has an infinite resistance and acts as an open switch but as the light starts falling on the photodiode, the resistance becomes low and when the full intensity of light falls on the photodiode then its resistance becomes zero and it starts acting like a closed switch.

OP-AMP:

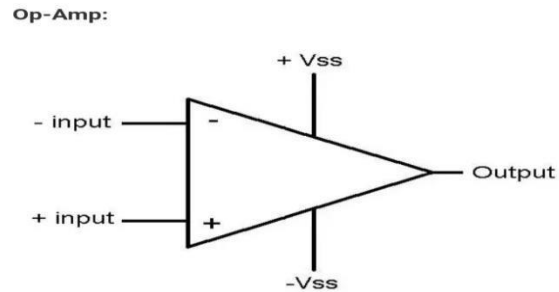


Fig 7.3

OP-AMP stands for operational amplifier. It is a DC-coupled high gain amplifier with differential inputs and single output. Typically the output of the op-amp is controlled by either negative or positive feedback. Due to the fact that it performs several operations like addition, subtraction, etc. It is named as operational amplifier. It has two inputs pins and one output pin.

8. IR Transmitter:

Infrared Transmitter is a light emitting diode (LED) which will emits infrared radiations. Hence, they are called as IR LED's. Even though an IR LED looks like a normal LED, the radiation emitted by it is invisible to the human eye.

The picture of a typical infrared LED is shown below



Fig 8.1

There are different types of infrared transmitters depending on their wavelengths, output power and response time.

A simple infrared transmitter can be constructed using an infrared LED, a current limiting resistor and also power supply.

IR Transmitter can be found in several applications. Some applications require infrared heat and the best infrared source is infrared transmitter. When infrared emitters are used with Quartz, solar cells can be made.

Distinguishing Between Black and White colours:

It is a universal that all the black colours absorb the entire radiation incident on it. Based on this principle, the second positioning of the sensor couple can be made. The IR LED and the photodiode are placed side by side. When the IR transmitter emits infrared radiation, since there is no direct line of contact between the transmitter and receiver, the emitted radiation must reflect back to the photodiode after hitting any object. The surface of the object can be divided into two types: reflective surface and non-reflective surface.

If the surface of the object is reflective in nature i.e. it is white or other light colour, most of the radiation incident on it will get reflected back and reaches the photodiode. Depending on the intensity of the radiation reflected back to the current flows in the photodiode.

If the surface of the object is non-reflective in nature i.e. it is black or other dark colour, it absorbs almost all the radiation incident on it. As there is no reflected radiation there will be no radiation incident on the photodiode and the resistance of the photodiode remains higher no current to flow. This is the main situation is similar to there being no object at all.

The pictorial representation of the above scenarios is shown below:

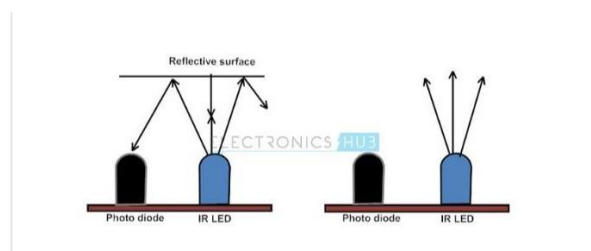


Fig 8.2

The positioning and enclosing of the IR transmitter and the Receiver is very important. Both the transmitter and the receiver must be placed at a certain angle, so that the detection of an object happens properly. This angle is the directivity of the sensor which is ± 45 degrees.

The directivity is shown below:

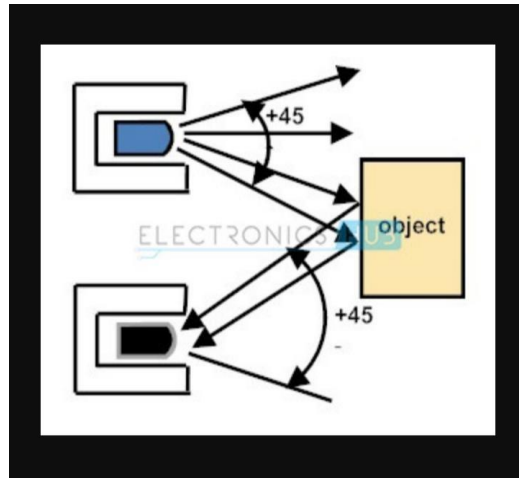
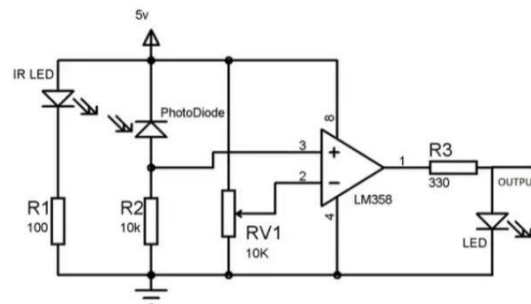


Fig 8.3

In order to avoid reflections from surrounding objects other than the object, both the IR transmitter and the IR receiver must be enclosed properly. Generally the enclosure is made of plastic and is painted with the black colour.

Working:

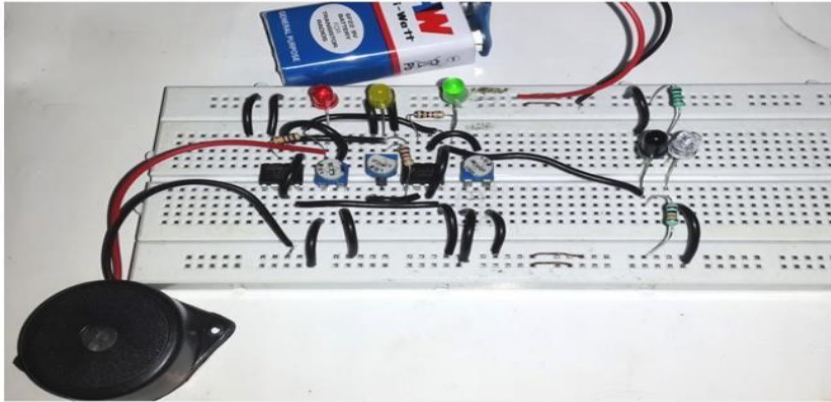


We know that the white surface reflects all the radiations falls on it whereas the black color absorbs them. When the supply is given to IR sensor, LED starts emitting light radiations. If the surface is of white color then it reflects all the radiations. As these radiations start falling on the photodiode which is connected in reverse bias the resistance of the photodiode starts decreasing rapidly and the voltage drop across the diode also decreases. The voltage at pin 3 starts increasing, as it reaches just beyond the voltage pin 2 the comparator gives high output. In case of the black surface, LED emits light but it is not reflected by the surface. Hence the comparator gives low output.

Chapter: 5

Results and Discussion

Results:



Reverse Car Parking Circuit using IC LM358

Discussion:

The effective range is proportional to the power of the transmitted pulses. As we have found out from our circuit, that as the distance of the car from the wall got less and less, the reflected IR needed less time and also it brought back a more intensified beam back reflected.

This system is placed at the rear of the car and sensors front side towards the obstacle. Now suppose car is moving back towards the wall or obstacle in the parking slot. If distance between car and obstacle is more than 15cm then no LED will glow. Now if car moves towards the obstacles and suppose green light turned on, it means car is about 15cm away from the obstacle. Now car is moving more close towards the obstacle and yellow light appears or turned on it means car is about 10cm away from the obstacle. Now car is moving closer towards the obstacle and red light appears it means car is about 5cm away from the obstacle and same time buzzer start beeping. Buzzer and red light indicates that the car need to stop now otherwise car may be damaged.

To test the accuracy of the device we measured the actual distance between the sensors and the object with ruler and compared that to the distance reading which we have expected from the calculations.

Obstacle v/s Vehicle	LED status	Reference Voltage	Distance
not close	All OFF		Greater than 15 cm
Close	Green ON	2.0 Volt	About 15 cm
More Close	Yellow ON	4.0 Volt	About 10 cm
More Close	Red ON	6.0 Volt	About 5 cm
Touch	Car Damaged		About 0 cm

Table 5.1 Distance intervals and corresponding lighted LEDs

Chapter: 6

Conclusion and Future Scope

Conclusion:

Using this circuit, the efficiency in alleviating the traffic problem that arises especially in the city. Where traffic congestion and the insufficient parking spaces are undeniable.

Future Scope:

New and better technology for the cars and other automobiles, with both visual as well as audible feedback.

This is a valuable car accessory technology because not only is it a great addition to our high-tech car gadgets, it greatly lowers the risk of vehicle accidents.

Advantages:

1. By this parking area can be easily identified so the traffic is reduced and also carbon emission is also reduced.
2. Low cost
3. Low power consumption
4. More accurate and well suited for real-time implementation
5. Helps the driver a better and convenient for parking.

Applications:

1. This circuit can be used in automobiles to park the vehicle safely.
2. We can use this circuit to measure the distance.
3. We can also use this circuit as IR Liquid Level Detector by making few modifications.

Limitations:

1. IR receiver may receive the normal light. As a result, parking sensor may not work properly. 2. We should arrange IR sensors accurately; otherwise they may not detect the obstacle.

Reference:

www.circuitdigest.com

www.electronicshub.com

Reverse Car Parking Sensor

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